

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(amorphous near silicon) with (molecular near organic near compound)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/23 09:28
L2	49	(amorphous near silicon) and (molecular near organic near compound)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/23 09:28
S1	1601	257/40.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:31
S2	1362	S1 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S3	184	S2 and (gate near (oxide insulat\$3 dielectric) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:47
S4	13	S2 and (gate near oxide near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S5	388310	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:52
S6	44641	S5 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S7	27	S6 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film))) with (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:59

S8	817	organic adj ((thin adj film adj transistor\$1) TFT\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:59
S9	2	S8 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film)) with (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:03
S10	818	organic adj ((thin adj film adj transistor\$1) TFT\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:53
S11	12	S10 and ((gate near oxide near (layer film)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 16:08
S12	3	("5347144" "5946551" "5981970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:15
S13	6	("4724106" "5075738" "5206525" "5347144" "5625199" "5705826").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:16
S14	2	("5347144" "5355235").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:18
S15	2	("4873556" "5107308").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:20
S16	22	S10 and (((gate near oxide) (Ta2O3 Al2O3)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:25
S17	3	("5347144" "5625199" "5981970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:33
S18	818	organic adj ((thin adj film adj transistor\$1) TFT\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:07

S19	7	S18 and (molecular near organic near compound)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:07
S20	12	("20030056720" "5402748" "5468519" "5554220" "5736073" "5953828" "6207239" "6232157" "6278127" "6326640" "6337102" "6664137").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 17:21
S21	13	("4021835" "4065781" "5247193" "5315129" "5331183" "5347144" "5350459" "5355235" "5442198" "5500537" "5525811" "5574291" "5612228").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 17:22
S22	5348	organic adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:56
S23	14	S22 and (molecular near organic near compound)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:07
S24	2	(organic adj semiconductor) with (molecular near organic near compound)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:31
S25	396	((intermediate inorganic) adj (material layer film)) with (gate near (oxide insulat\$3) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:43
S26	22	S25 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 19:09
S27	66	((intermediate inorganic) adj (material layer film)) with between with (gate near (oxide insulat\$3) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 19:07

S28	1	S27 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 18:43
S29	119	(SiO2 SiN SiON) with between with (gate near (oxide insulat\$3) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:46
S30	0	S29 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 19:09
S31	0	S29 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 19:09
S32	24	S29 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 19:10
S33	1	(inorganic SiO SiN SiON) with between with (gate near oxide near (film layer)) with (gate near (insulat\$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:48
S34	18	(inorganic SiO SiN SiON) same between same (gate near oxide near (film layer)) same (gate near (insulat\$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:52
S35	1316	(inorganic SiO SiN SiON) and between and (gate near oxide near (film layer)) and (gate near (insulat\$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:14
S36	6	S35 and (organic adj ((thin adj film adj transistor\$1) TFT\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 08:53

S37	10	S35 and organic adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36
S38	87	(inorganic near (material\$1 layer film)) and between and (gate near oxide near (film layer)) and (gate near (insulat\$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36
S39	85190	(inorganic near (material\$1 layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:35
S40	904	S39 and organic adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:36
S41	1	S40 and (gate near oxide near (film layer)) with (gate near (insulat\$3 dielectric) near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/23 06:58
S42	10	S40 and (gate near oxide near (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/08 09:37
S43	51	(gate near oxide near (film layer)) with (oxidiz\$3 near2 gate near electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/23 09:26
S44	8	("4368523" "4820222" "4938567" "5062690" "5517341" "5532853" "5648826" "5715025").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/23 07:20
S45	4	((("5532853") or ("5648826"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/09/23 07:52